

**IN THE SPECIFICATION:**

The specification has been amended as follows:

Page 15, after the last line, insert new paragraph as follows:

Thus, the present invention provides a method for fabricating an integrated electronic device having an electric connection between a first electrode of a first substrate and a second electrode of a second substrate comprising the steps of:

forming a first metal layer on a surface of a first electrode on a first substrate, the first metal layer capable of composing an eutectic alloy with a gallium (Ga);

forming a bump of Ga-rosin mixture on the first metal layer selectively; and

forming the electric connection between the first electrode and the second electrode by heating the bump of Ga-rosin mixture maintaining the bump of the Ga-rosin mixture in contact with the second electrode to react gallium in the Ga-rosin mixture with the first metal layer into the alloy capable to adhere to the first and second electrodes. In this method for fabricating an integrated electronic device, in the first metal layer is selected from the group consisting of tin, indium, silver, and zinc.

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IN THE CLAIMS:

Claims 39 and 41 have been amended as follows:

39. (Amended) A method for fabricating an integrated electronic device having an electric connection connecting a first electrode of a first substrate with a second electrode of a second substrate, surfaces of the first and the second electrodes having repellant and adhesive tendencies to molten metal, respectively, the method comprising the steps of:

forming [a] first and second soldering metal bumps on the surfaces of the first and second electrodes by depositing first and second soldering metals through [the] first and second masks, respectively, a melting temperature of the first soldering metal bump being higher than a melting temperature of the second soldering metal bump;

aligning the first and second soldering metal bumps to each other, and then keeping both in contact with each other; and

heating the first and second soldering metal bumps to melt the second soldering metal bump at a connection temperature lower than the melting temperature of the first soldering metal bump and solidifying the second soldering metal to form an electric connection between the first and second electrodes.

41. (Amended) A method for fabricating an integrated electronic device according to claim 39, wherein the first and second soldering metal bumps essentially consist of an alloy of Pb and Sn, wherein Pb is contained less in the first soldering metal bump than in the second soldering metal bump.